# Hex 3-State Noninverting Buffer with Common Enables and LSTTL Compatible Inputs

# **High-Performance Silicon-Gate CMOS**

The MC74HCT365A is identical in pinout to the LS365. The device inputs are compatible with LSTTL outputs.

This device is a high-speed hex buffer with 3-state outputs and two common active-low Output Enables. When either of the enables is high, the buffer outputs are placed into high-impedance states. The HCT365A has noninverting outputs.

#### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 90 FETs or 22.5 Equivalent Gates
- These are Pb-Free Devices\*



#### ON Semiconductor®

http://onsemi.com

#### MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

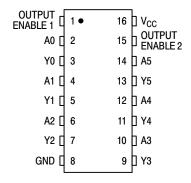


Figure 1. Pin Assignment

# A1 $\frac{4}{4}$ $\frac{5}{5}$ Y1 A2 $\frac{6}{10}$ $\frac{7}{7}$ Y2 A3 $\frac{10}{10}$ $\frac{9}{9}$ Y3 A4 $\frac{12}{11}$ Y4 A5 $\frac{14}{13}$ Y5 OUTPUT ENABLE 1 $\frac{1}{15}$ OUTPUT ENABLE 2 PIN 8 = GND

3

Figure 2. Logic Diagram

#### **FUNCTION TABLE**

	Output		
Enable 1	Enable Enable 1 2		Y
L	L	L	L
L	L	Н	Н
Н	X	X	Z
X	Н	Х	Z

X = don't care

Z = high impedance

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCT365ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HCT365ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HCT365ADTG	TSSOP-16* (Pb-Free)	96 Units / Rail
MC74HCT365ADTR2G	TSSOP-16* (Pb-Free)	2500 Units / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced	- 0.5 to + 7.0	V	
V <sub>in</sub>	DC Input Voltage (Referenced to	$-0.5$ to $V_{CC}$ + $0.5$	V	
V <sub>out</sub>	DC Output Voltage (Referenced	$-$ 0.5 to $V_{CC}$ + 0.5	V	
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA	
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA	
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GN	ID Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	<b>–55</b>	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 1)	0	500	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$\begin{aligned} &V_{out} = V_{CC} - 0.1 \text{ V} \\ & I_{out}  \leq 20  \mu\text{A} \end{aligned}$	4.5 to 5.5	2.0	2.0	2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	4.5 to 5.5	0.8	0.8	0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	4.5	4.4	4.4	4.4	٧
		$V_{in} = V_{IH}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5	0.1	0.1	0.1	V
		$V_{in} = V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.40	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	4.5	±0.1	±1.0	±1.0	μА
l <sub>OZ</sub>	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	4.5	±0.5	±5.0	±10	μА
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	4.5	4	40	160	μА
$\Delta I_{CC}$	Additional Quiescent Supply	V <sub>in</sub> = 2.4V, Any One Input		≥ <b>-55</b> °C	25 to	125°C	
	Current	$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0\mu A$	5.5	2.9		2.4	mA

# AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_{\rm f}$ = $t_{\rm f}$ = 6 ns)

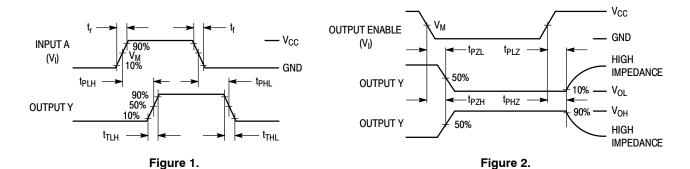
			Guaranteed Limit			
Symbol	Parameter	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	4.5	24	30	36	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	4.5	44	55	66	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	4.5	44	55	66	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	4.5	12	15	18	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	_	15	15	15	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*	60	pF

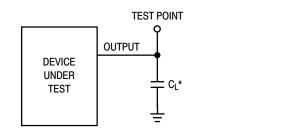
<sup>\*</sup>Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

#### **SWITCHING WAVEFORMS**

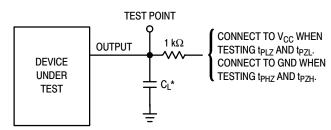
 $(V_I = 0 \text{ to } 3 \text{ V}, V_M = 1.3 \text{ V})$ 



#### **TEST CIRCUITS**



\*Includes all probe and jig capacitance

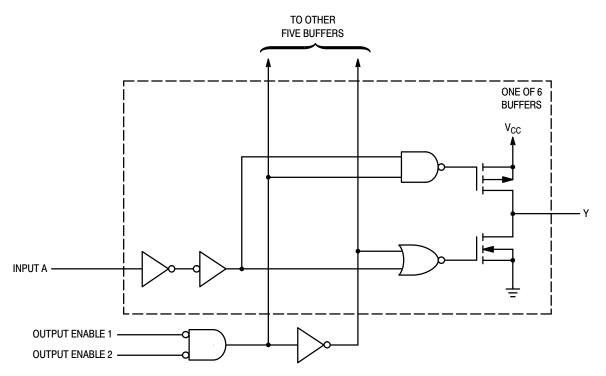


\*Includes all probe and jig capacitance

Figure 3.

Figure 4.

#### **LOGIC DETAIL**

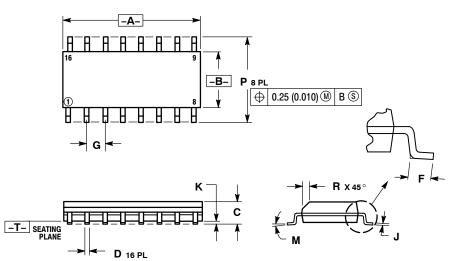






#### SOIC-16 CASE 751B-05 **ISSUE K**

**DATE 29 DEC 2006** 



⊕ 0.25 (0.010) M T B S A S

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.

- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION.
  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D
  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		
	COLLECTOR	PIN 1.	CATHODE	PIN 1.		PIN 1.	COLLECTOR, DYE #	1
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3	
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4	
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4	
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4	
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4	
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3	
12.	EMITTER	12.		12.	COLLECTOR, #3	12.	EMITTER, #3	
13.	BASE	13.		13.		13.	BASE, #2	RECOMMENDED
14.	COLLECTOR	14.	NO CONNECTION	14.		14.	EMITTER, #2	SOLDERING FOOTPRINT*
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8X
								<b>←</b> 6.40 <b>→</b>
STYLE 5:		STYLE 6:		STYLE 7:				
PIN 1.	DRAIN, DYE #1		CATHODE		SOURCE N-CH			16X 1.12 <
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPU	T)		<u> </u>
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU			1 16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,	<u>)</u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X 7	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH			
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		_	<del></del>
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)		
13.	GATE, #2	13.	ANODE	13.	GATE N-CH			
14.	SOURCE, #2		ANODE	14.				
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU	Τ)		PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			
								□□18   9 <del>+ □ + </del> <del> </del>
								DIMENSIONS: MILLIMETERS

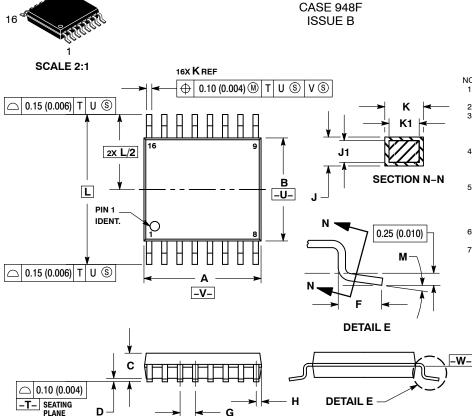
\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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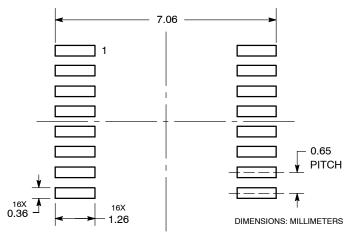
TSSOP-16 WB

#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABILE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
M	0 °	8°	0 °	8 °	

#### **RECOMMENDED** SOLDERING FOOTPRINT\*



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC** MARKING DIAGRAM\*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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